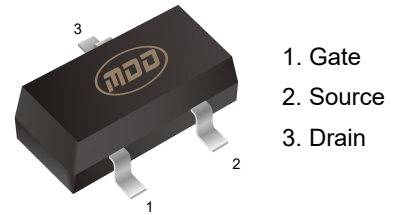


SOT-23

$V_{(BR)DSS}$	$R_{DS(on)Typ}$	$I_D Max$
-30V	45mΩ@-10V	-4.2A
	50mΩ@-4.5V	



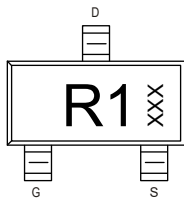
Features

High dense cell design for extremely low RDS(ON)
 Exceptional on-resistance and maximum DC current capability

Application

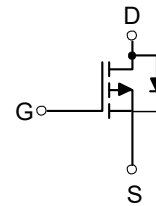
- Load/Power Switching
- Interfacing Switching

Marking



XXX:Date Code

Equivalent Circuit



Absolute Maximum Ratings ($T_A=25^{\circ}C$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	-30	V
Gate-Source Voltage	V_{GS}	±12	V
Continuous Drain Current	I_D	-4.2	A
Pulsed Drain Current (Note 1)	I_{DM}	-16	A
Power Dissipation(Note 2)	P_D	1.2	W
Thermal Resistance from Junction to Ambient(Note 2)	$R_{\theta JA}$	80	$^{\circ}C/W$
Junction Temperature and Storage Temperature	T_J, T_{stg}	-50 ~150	$^{\circ}C$

Notes: Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.



Ta = 25°C unless otherwise specified

Symbol	Parameter	Condition	Min	Typ	Max	Unit
V _{(BR)DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =-250μA	-30	--	--	V
I _{DSS}	Drain-Source Leakage Current	V _{DS} =-30V, V _{GS} =0V	--	--	-1	uA
I _{GSS}	Gate-Source Leakage Current	V _{GS} =±12V, V _{DS} =0V	--	--	±100	nA
V _{GS(TH)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =-250μA	-0.5	-0.8	-1.2	V
R _{DS(ON)}	Drain-Source On-State Resistance(Note 3)	V _{GS} =-10V, I _D =-4.1A	--	45	55	mΩ
		V _{GS} =-4.5V, I _D =-4A	--	50	65	mΩ
		V _{GS} =-2.5V, I _D =-1A	--	65	80	mΩ

Dynamic Electrical Characteristics

Symbol	Parameter	Condition	Min	Typ	Max	Unit
C _{iSS}	Input Capacitance	V _{DS} =-15V V _{GS} =0V f=1MHz	--	655	--	pF
C _{oSS}	Output Capacitance		--	65	--	pF
C _{rSS}	Reverse Transfer Capacitance		--	53	--	pF
Q _g	Total Gate Charge	V _{DS} =-15V	--	8.5	--	nC
Q _{gs}	Gate Source Charge	V _{GS} =-4.5V	--	1.8	--	nC
Q _{gd}	Gate Drain Charge	I _D =-4.2A	--	2.7	--	nC

Switching Characteristics

Symbol	Parameter	Condition	Min	Typ	Max	Unit
t _{d(on)}	Turn on Delay Time	V _{DS} =-15V V _{GS} =-10V I _D =-3A R _G =6Ω	--	7	--	ns
t _r	Turn on Rise Time		--	3.8	--	ns
t _{d(off)}	Turn Off Delay Time		--	35	--	ns
t _f	Turn Off Fall Time		--	10.5	--	ns

Source Drain Diode Characteristics

Symbol	Parameter	Condition	Min	Typ	Max	Unit
I _{SD}	Source drain current(Body Diode)	T _A =25°C	--	--	-2	A
V _{SD}	Drain-Source Diode Forward Voltage	I _S =-1A, V _{GS} =0V	--	--	-1	V

- Notes:**
- 1.Pulse width limited by maximum allowable junction temperature
 - 2.The value of P_D&R_{θJA} is measured with the device mounted on 1 in² FR-4 board with 2oz.Copper, double sided, in a still air environment with Ta=25°C.
 - 3.Pulse test ; Pulse width≤300us, duty cycles≤2%

Typical Characteristics

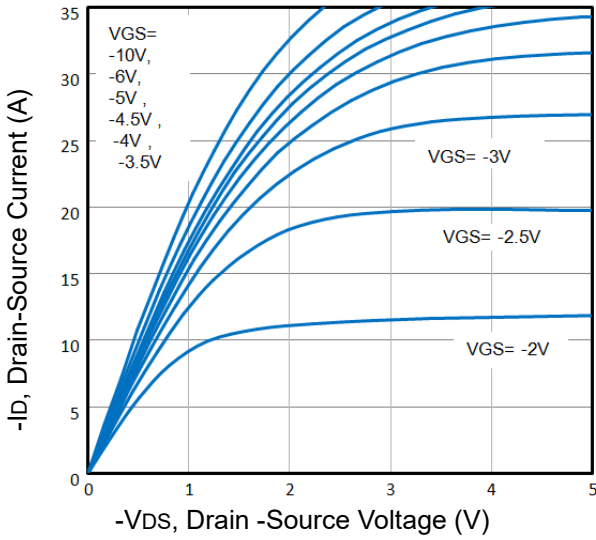


Fig1. Typical Output Characteristics

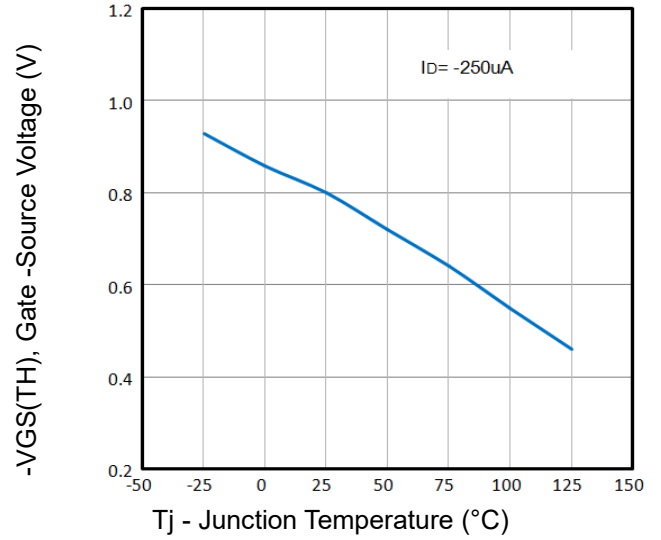


Fig2. Normalized Threshold Voltage Vs. Temperature

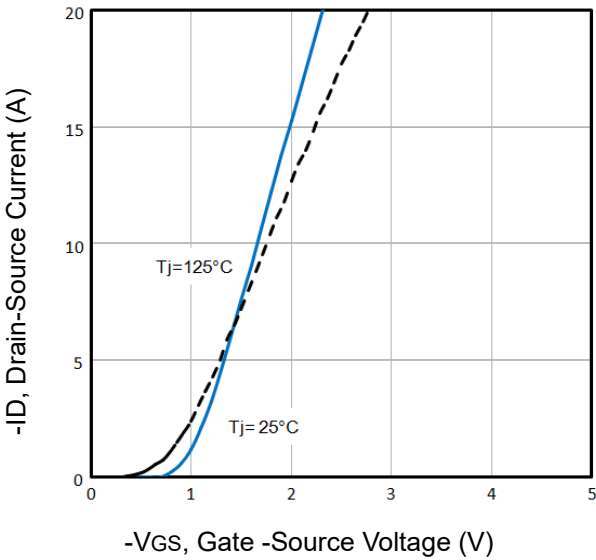


Fig3. Typical Transfer Characteristics

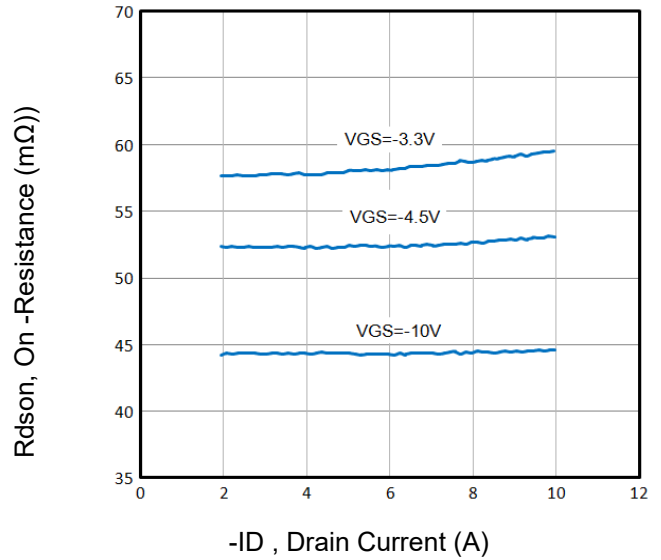


Fig4. On-Resistance vs. Drain Current and Gate

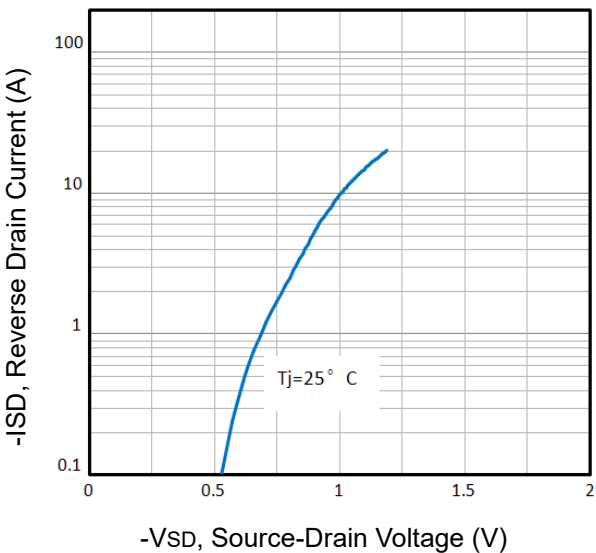


Fig5. Typical Source-Drain Diode Forward Voltage

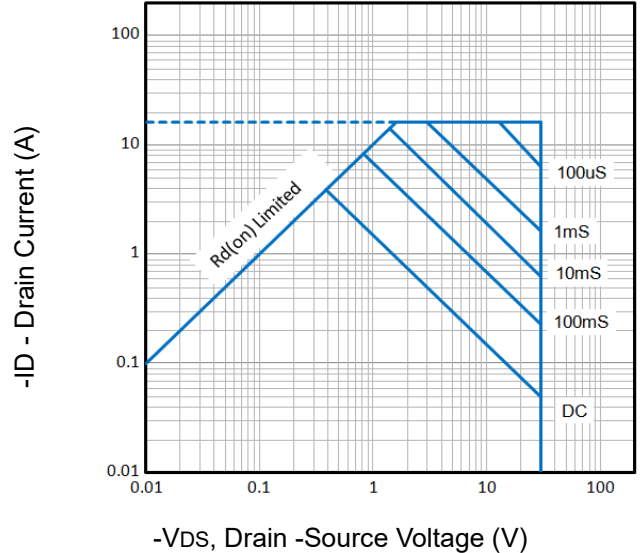


Fig6. Maximum Safe Operating Area

Typical Characteristics

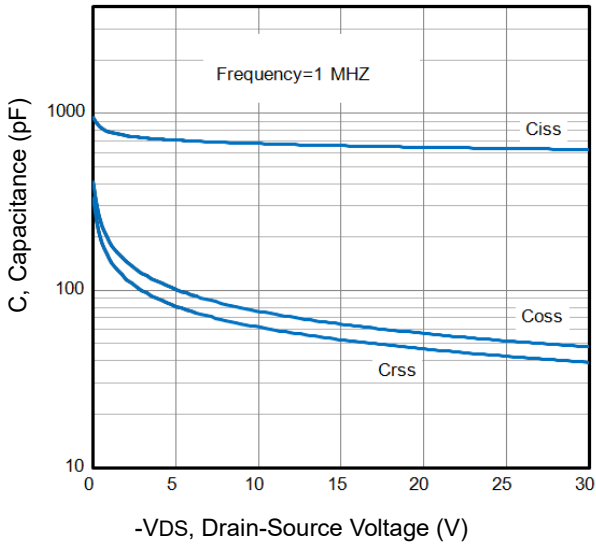


Fig7. Typical Capacitance Vs. Drain-Source Voltage

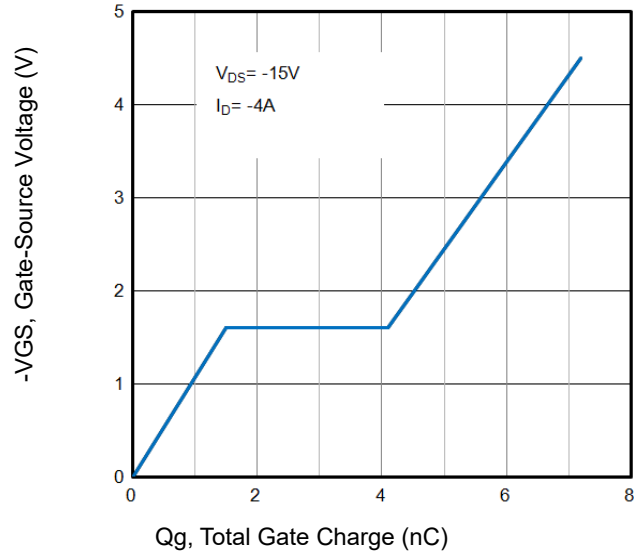


Fig8. Typical Gate Charge Vs. Gate-Source Voltage

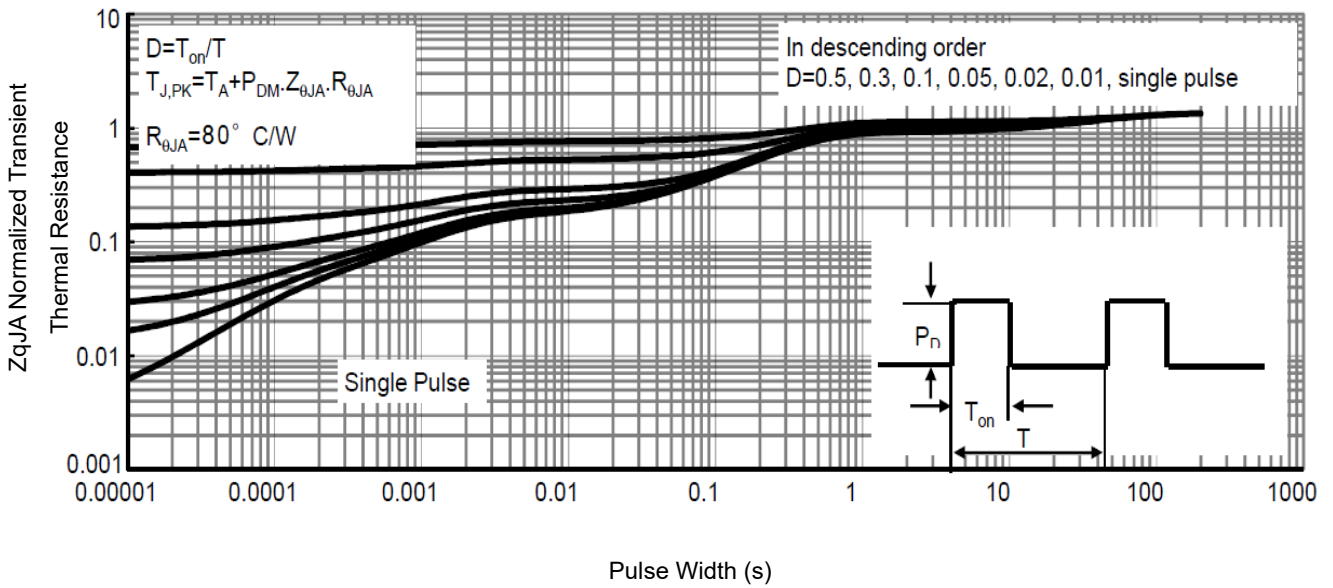


Fig9. Normalized Maximum Transient Thermal Impedance

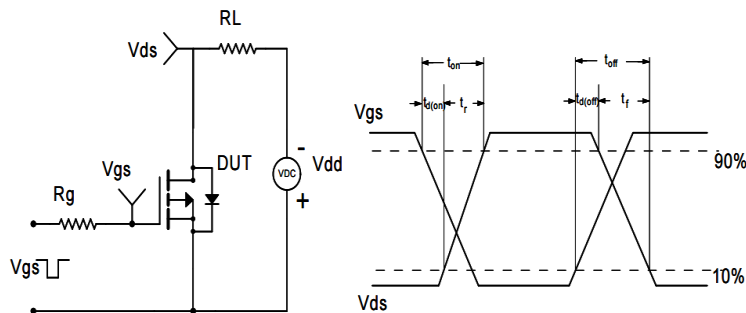
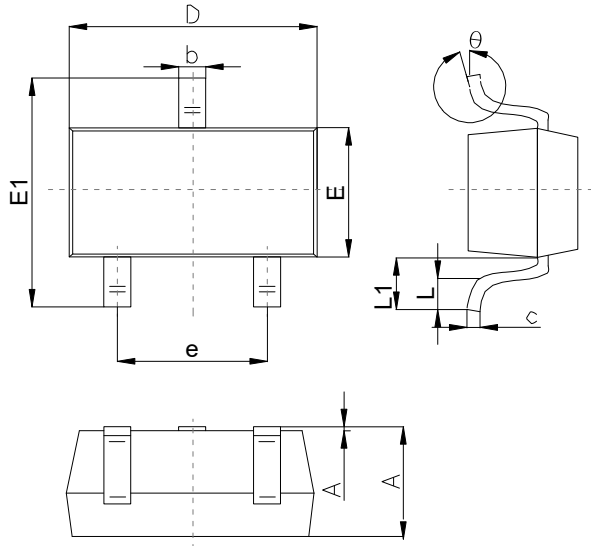


Fig10. Switching Time Test Circuit and waveforms

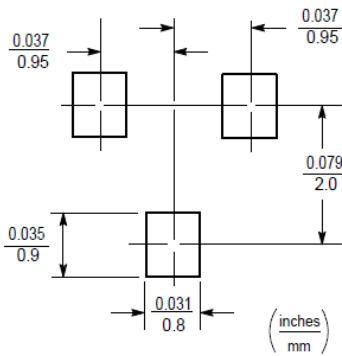
Outline Drawing

SOT-23 Package Outline Dimensions



Symbol	Dimensions In Millimeters		
	Min	Typ	Max
A	0.90		1.40
A1	0.00		0.10
b	0.30		0.50
c	0.08		0.20
D	2.80	2.90	3.10
E	1.20		1.60
E1	2.25		2.80
e	1.80	1.90	2.00
L	0.10		0.50
L1	0.4		0.55
θ	0°		10°

Suggested Pad Layout



Note:

1. Controlling dimension: in/millimeters.
2. General tolerance: ± 0.05 mm.
3. The pad layout is for reference purposes only.